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				Application Number	10/579,211 - Conf.# 6592
				Filing Date	May 12, 2006
				First Named Inventor	Toshihiko Shirasagi
				Art Unit	1756
				Examiner Name	Not Yet Assigned
Sheet	1	of	1	Attorney Docket Number	SON-3162

U.S. PATENT DOCUMENTS					
Examiner Initials*	Cite No. ¹	Document Number Number-Kind Code ² (if known)	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear

FOREIGN PATENT DOCUMENTS						
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NON PATENT LITERATURE DOCUMENTS			
Examiner Initials*	Cite No. ¹	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.	T ²
	CA	N. Koshida et al., "50-nm Metal Line Fabrication by Focused Ion Beam and Oxide Resists," Japanese Journal of Applied Physics, Vol. 30, No. 11B, November 1991, pp. 3246-3249	
	CB	S. M. Gorwadkar et al., "SiO ₂ /c-Si Bilayer Electron-Beam Resist Process for Nano-Fabrication," Japanese Journal of Applied Physics, Vol. 35 (1996), Part 1, No. 12B, pp. 6673-6678, December 1996	
	CC	S. A. Kostyukevych, "Investigations and modeling of physical processes in inorganic resists for the use in UV and laser lithography," Institute of Physics of Semiconductors, National Academy of Sciences Prospect Nauki 45, Kiev, 252028, UKRAINE, part of the SPIE Conference on Inorganic Optical Materials, California, SPIE Vol. 3424, July 1998	

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